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FCP130, IFCP65 and incorporation in RD53A

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- Cluster size: ~4 (average)
 - Cluster size and shape varies significantly over pixel detector:
 - Middle barrel, End barrel, End cap disks, tracks from collision point, Machine background/halo, loopers, etc.
- Rate: Worst case HL-LHC (layer locations as in Phase1)
 - **Layer 1** (3.0cm): ~500MHz/cm² tracks -> **~2GHz/cm² hits**
 - Layer2 (6.8cm): ~½ of layer 1
 - Layer3 (10.2cm): ~½ of layer 2 -> ~¼ of layer 1
 - **Layer4** 16.0cm) : ~½ of layer 3 -> **~1/10 of layer 1** (50MHz/cm² tracks, 200MHz/cm² hits)
 - End-caps ?
- Pixel chip: ~6.5 cm²
- Pixel size: ~25x100um = 2500um²
 - Or 50um x 50um (same area but square)
 - (50um x 100um if more area required per pixel, No major effect on readout rate)
- Pixel regions: 4 x 4 or 2 x 2
- Pixels per chip: ~256k
- Tracks/hits per chip per Bx:
 - **Layer 1**: 50KHz/pixel, 75 tracks/IC/Bx, **300hits/IC/Bx**
 - **Layer 4**: 5KHz/pixel, 7.5 tracks/IC/Bx, **30hits/IC/Bx**
- L1 Trigger: 1MHz, 20us (10us) now baseline for all new Phase2 detectors

Preliminary specification*

Specification	
Pixel size	25x100 μm^2 ; 30x100 μm^2 ; 50x50 μm^2
Sensor	2D, 3D, Diamond, MAPS ?
Chip size	> 2cm x 2cm
Transistors	~1G
Hit rate	1-2 GHz/cm ²
Hit memory per chip	>16Mb
Trigger rate	1MHz (CMS)
Trigger latency	6 - 20us
Readout rate	~5Gb/s per chip (inner)
Radiation	1Grad
Technology	65nm ?
Architecture	Digital
Power	¼ - ½ W/cm ² ?

RD53:

- Common technology platform for 65nm pixel chips
- Working groups: Radiation qualification, Analog design, Basic building blocks (IP), Simulation and verification framework, top level, etc.
- R&D collaboration with clearly defined goals: Project.
- A common or two different pixels chips can be made for CMS & ATLAS

*RD 53 Collaboration
-Borrowed from
J.Christiansen



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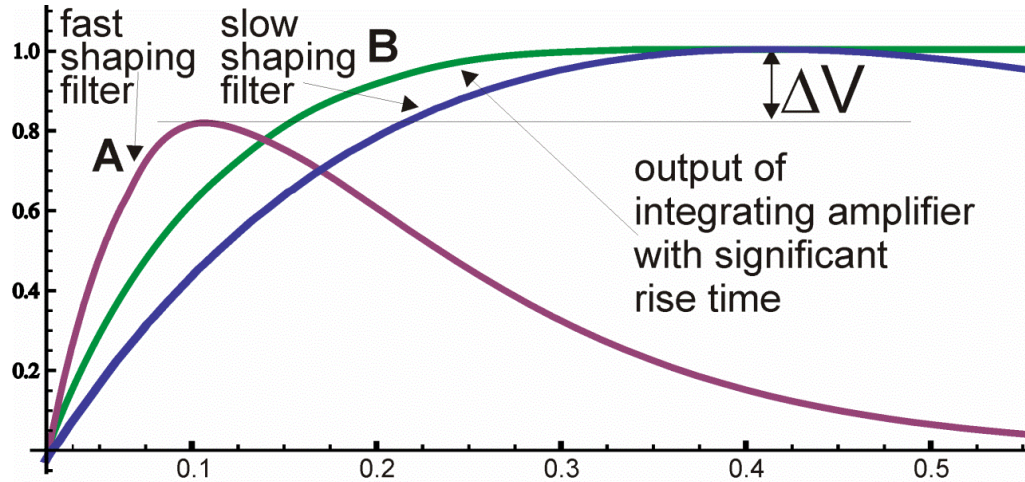
Fermi CMS Pixels (FCP130)

Fermi CMS Pixel (FCP130)- Design of a test CMS pixels chip

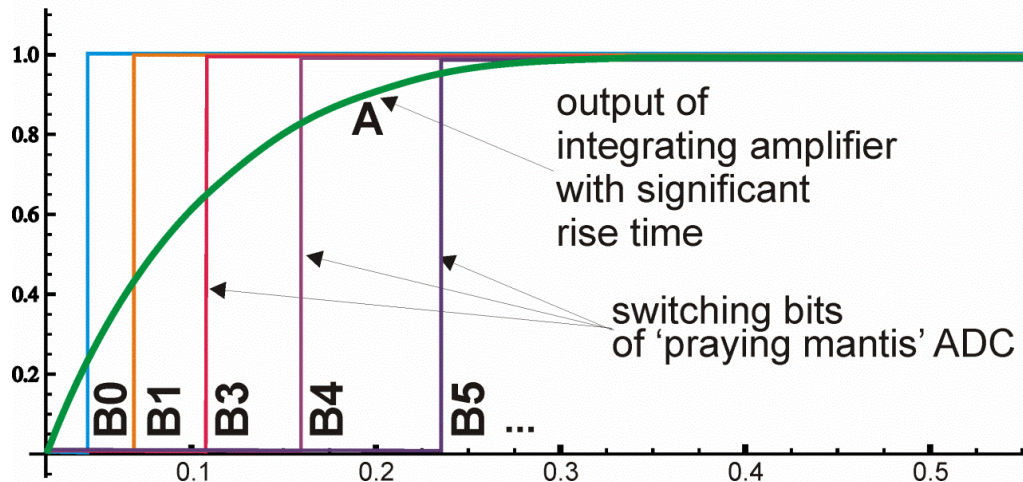
- **Test platform of Synchronous frontend with an Asynchronous output data flow**
- **Technology platform: GF130nm – Preliminary architectural investigation before 65nm.**
- ASIC size: 5.5 mm x 8.5 mm
- Pixel size: 30 μm x 100 μm (Analog part: 20 μm x 100 μm ; Digital Part: 10 μm x 100 μm)
- Rows x Columns: 48 x 160 (4 columns are grouped to create a superColumn (192 pixels))
- Each ASIC has 40 super columns.
- Analog Pixel options:
 - 1) Preamplifier + 3 bit Flash ADC + hit comparator (independent of ADC to get hit in the processing – to be reviewed on final realizations)
 - 2) Preamplifier + 3 bit ADC based on asynchronous conversion using in-pixel oscillator triggered by signal (more power consumption but more compact + perspectives for other uses)
- Digital Pixel: 8:3 bit encoder, hit processor, priority encoder for data sparsification
- End of column: FIFO to daisy chain then asynchronous data transfer through CONFLUX

Basic concepts: Synchronous front-end ?

- ✓ The Analog Front-End includes a **charge preamplifier** and **synchronous comparators** used for A-to-D conversion **within one BXClk period**



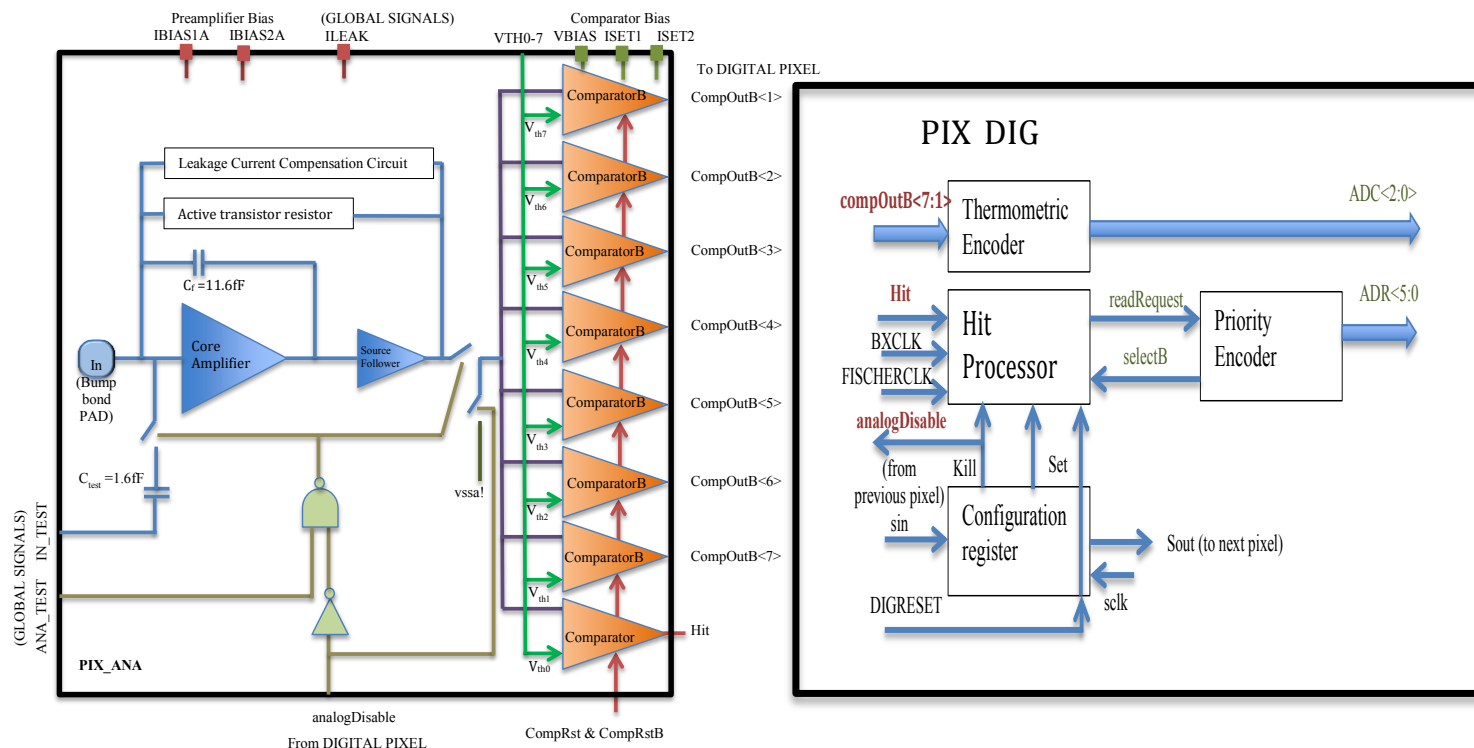
Fast shaping may worsen S/N due to ballistic deficit



Conversion begins as soon as charge starts being integrated and continues until signal reaches maximum or conversion time is over.

→ no dead time for conversion

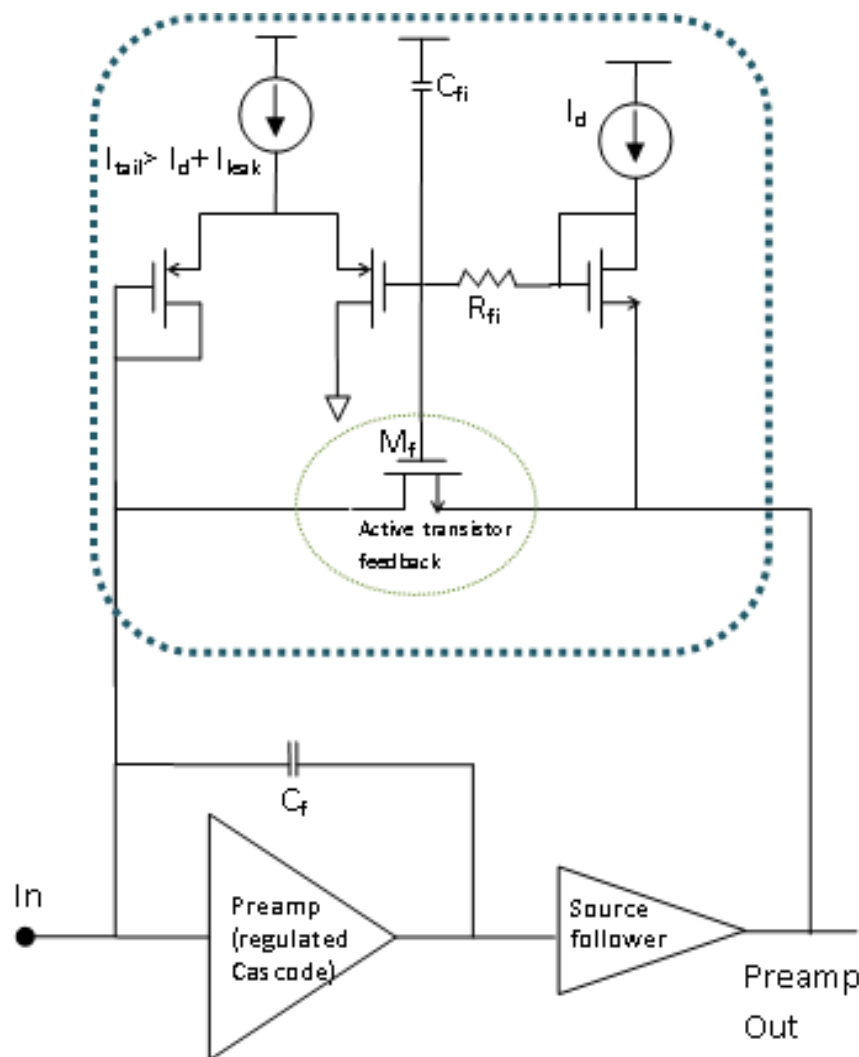
Pixel Architecture



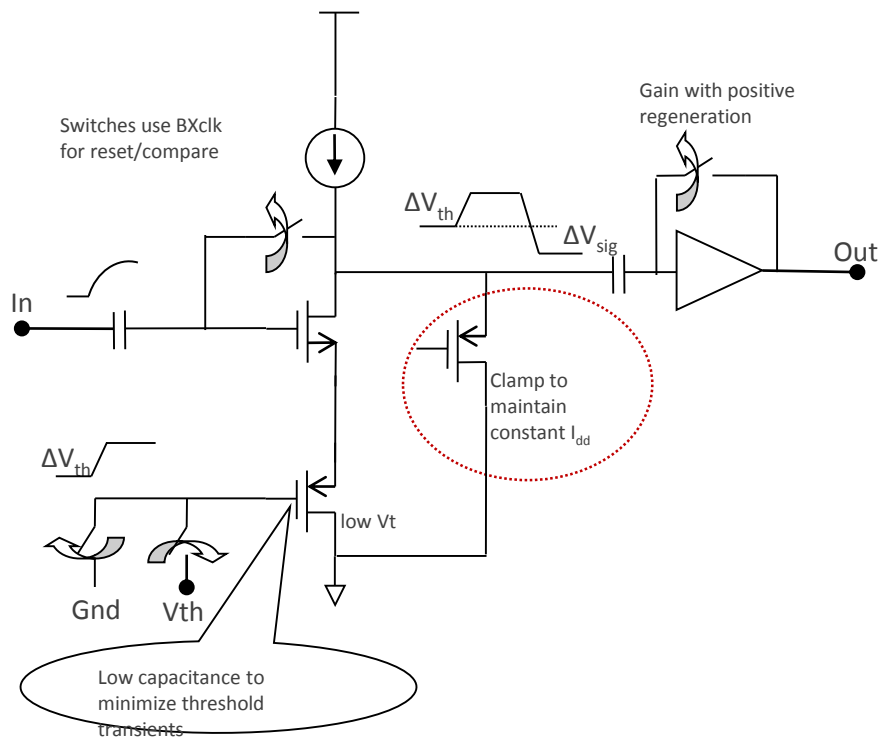
- Synchronous front-end (utilize BXClk time structure)
- No continuous time filtering
- Insensitivity to absolute design parameters (e.g. shaping time)
- Increased noise immunity – digital conversion immediately after preamplifier
- Data Conversion within 1 BXClk cycle
- Processing insensitive to pileups

Preamplifier

- Dynamic range 0.25fC – 2.5fC
- Power Consumption : 5 μ A x 1.5V
- Regulated Cascode design
- Feedback capacitor : 11.58fF
- Active transistor resistor feedback
 - Large signals behaves as a constant current source
 - Small signals $R_f = 1/g_m$
- Leakage current compensation upto 5nA
- AC coupled to comparator
- Preamp, return to baseline is longer than 200ns, but only has to prevent output level from saturating



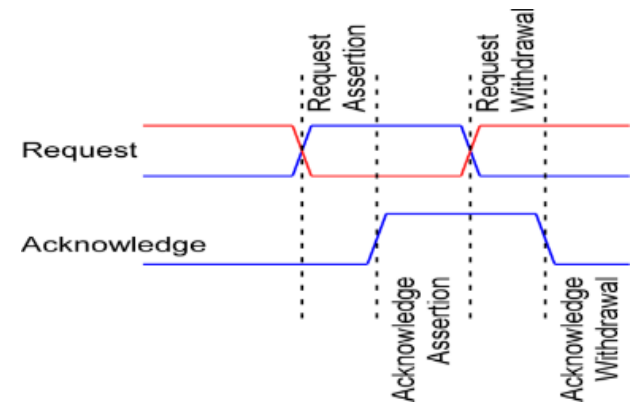
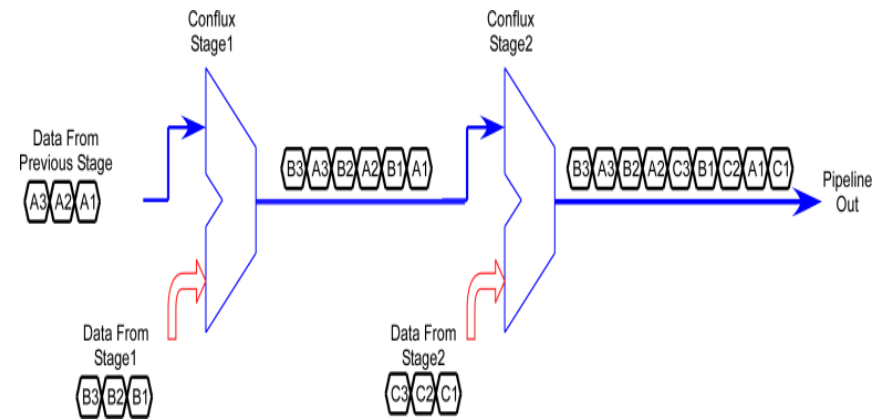
Comparator



- Compact, single-ended architecture.
- Auto-zeroed, “lurk-trigger-done” – praying mantis.
- Correlated double sampling
- Does not require trimming DACs
- 12.5ns reset phase; 12.5ns active comparison.
- Low-power, fast, insensitive to corners
- 2 stage design with additional gain and positive regeneration in 2nd stage.
- Require distribution of BXclk across a large chip

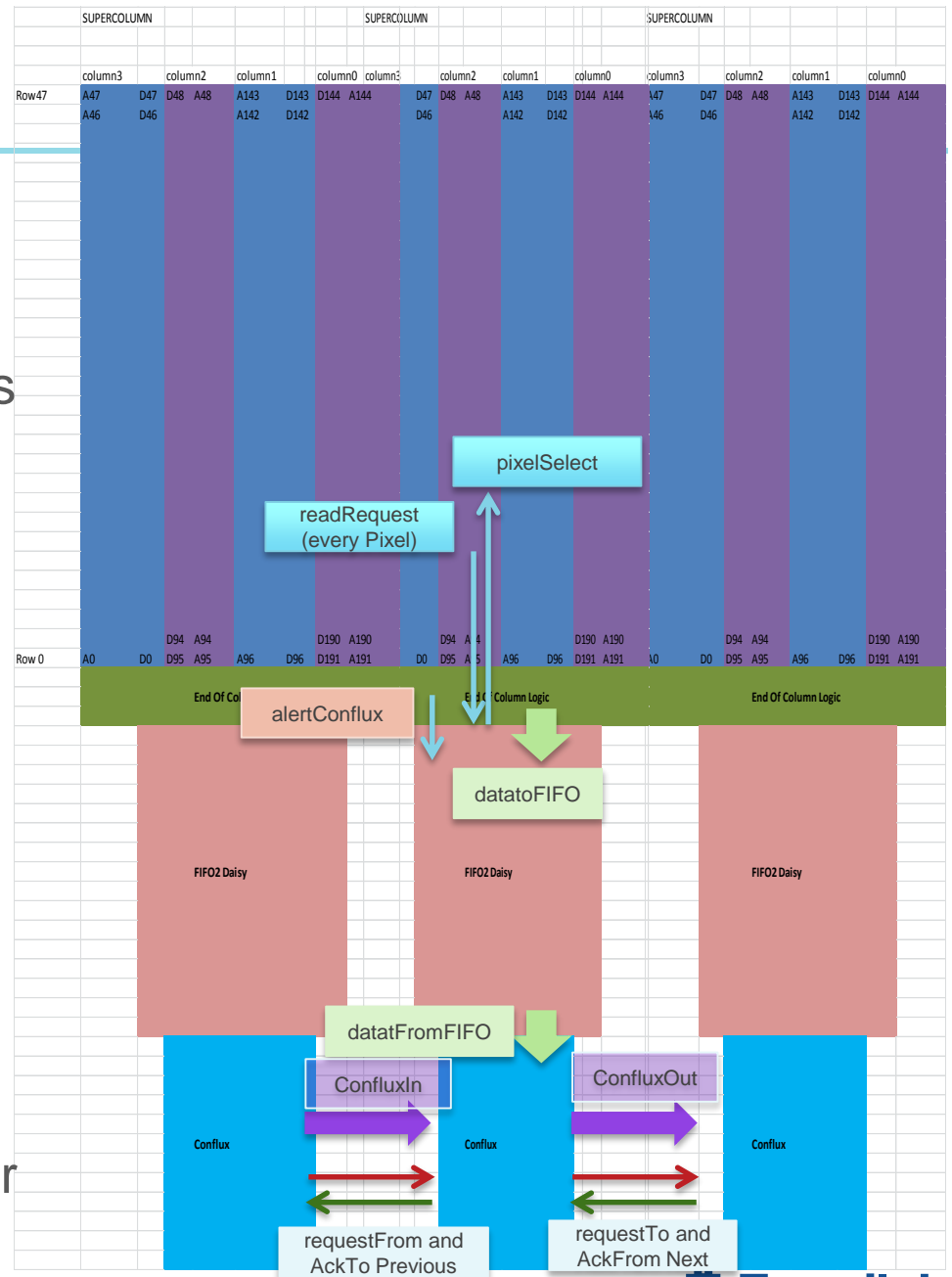
Conflux: Asynchronous Data transfer

- Conflux is based on a classic 4-phased bundled-data asynchronous protocol (Request Assertion → Acknowledge Assertion → Request Withdrawal → Acknowledge Withdrawal).
- Conflux blocks across several chips and/or boards can be chained together and no clock is necessary.
- No global control signals are necessary either.
- Each link in the chain passes on data from its predecessor to its successor and adds its own data to the stream.
- Each Conflux readout can be seen as an asynchronous 2-to-1 multiplexor for Time Division Multiplexing (TDM).

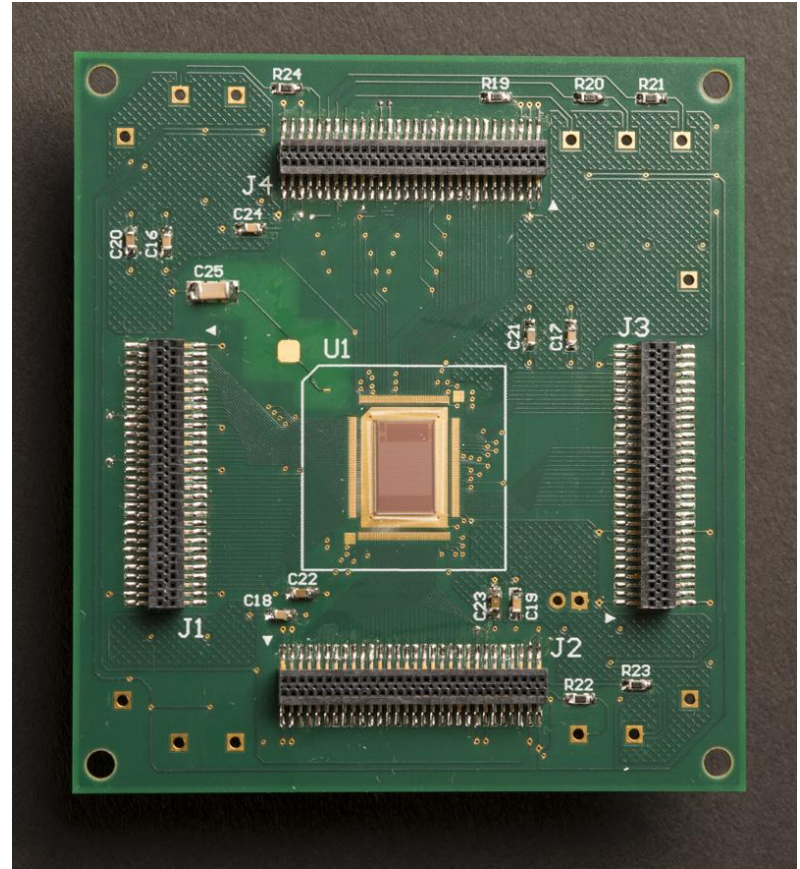
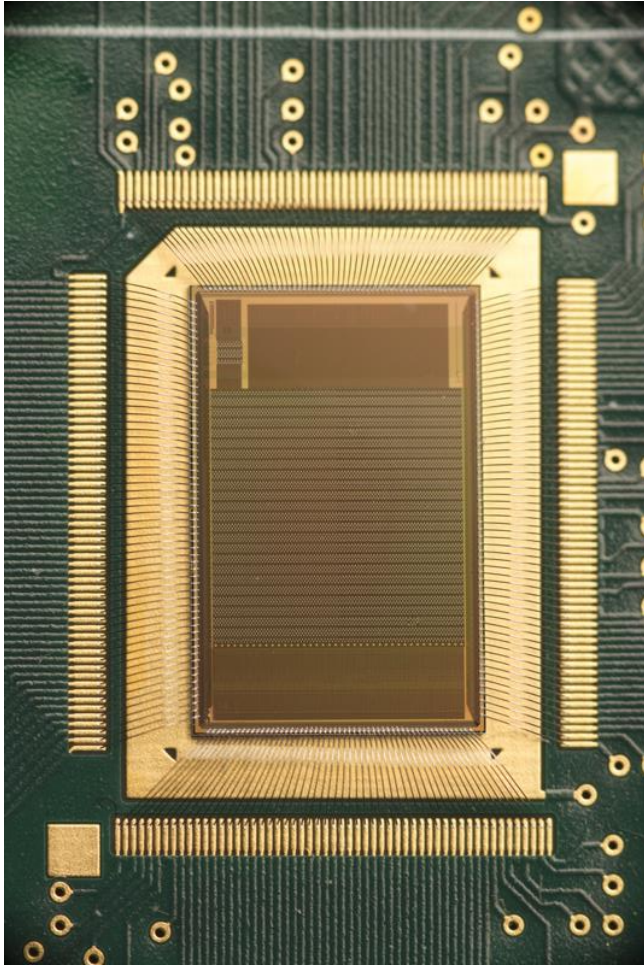


ASIC dataflow

- Hit signal from each pixel in a superColumn is “ORed” to create “alertConflux”
- Every pixel which is hit, generates a “readRequest”
- This is cancelled if the End of Column Logic issues a “selectPixel” signal at posedge of each “rStrobe”
- During 1 BXC1k cycle, alertConflux remains active until all pixels which are active are read and data is transferred to FIFO2daisy. This then resets
- Data from FIFO2daisy is transferred to Conflux using a four phase asynchronous scheme



FCP130

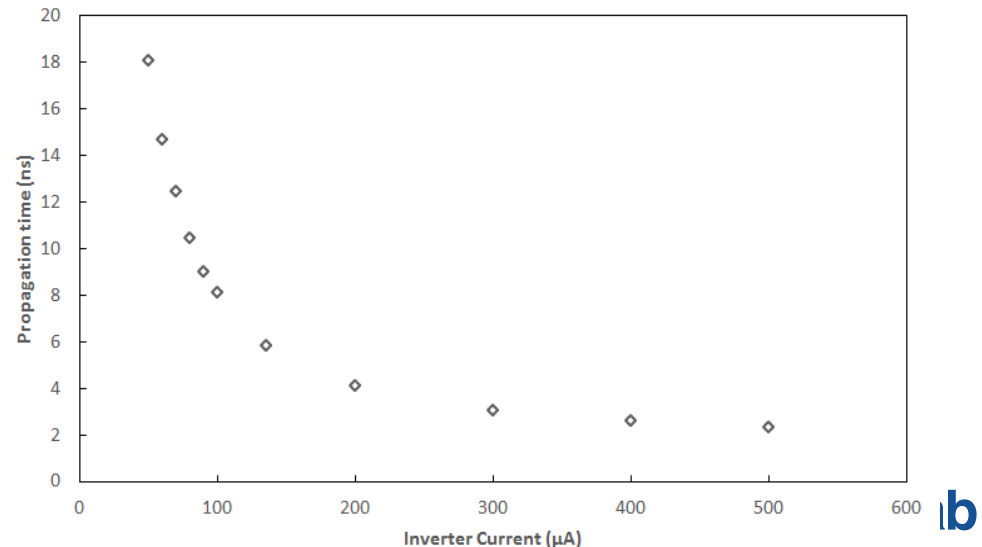


FCP130: Single pixel tests

- Successful Preliminary Qualitative analysis
 - Preamplifier response can be monitored; change of current is feedback loop changes the return to baseline.
 - All comparator response times are changing with change in threshold voltage.

FCP130: other functional tests

- Configuration register is able to able to correctly program the pixels
- The serial mode of transfer in FIFO 2 daisy can correctly send data Out
- The Spy signals for last superColumn (Pixel Hit, ADC value and address can be correctly monitored)
- Asynchronous data transfer (Conflux) was successfully verified



FCP130: issues and next steps

- Antenna diodes – were shorted to the substrate
- Floating deep nwell's
- Due to layout errors detailed analog tests of the entire matrix could not be characterized
- FCP130_v2 with bug fixes and enhanced versions of the preamplifier and comparator is being submitted Dec 2016



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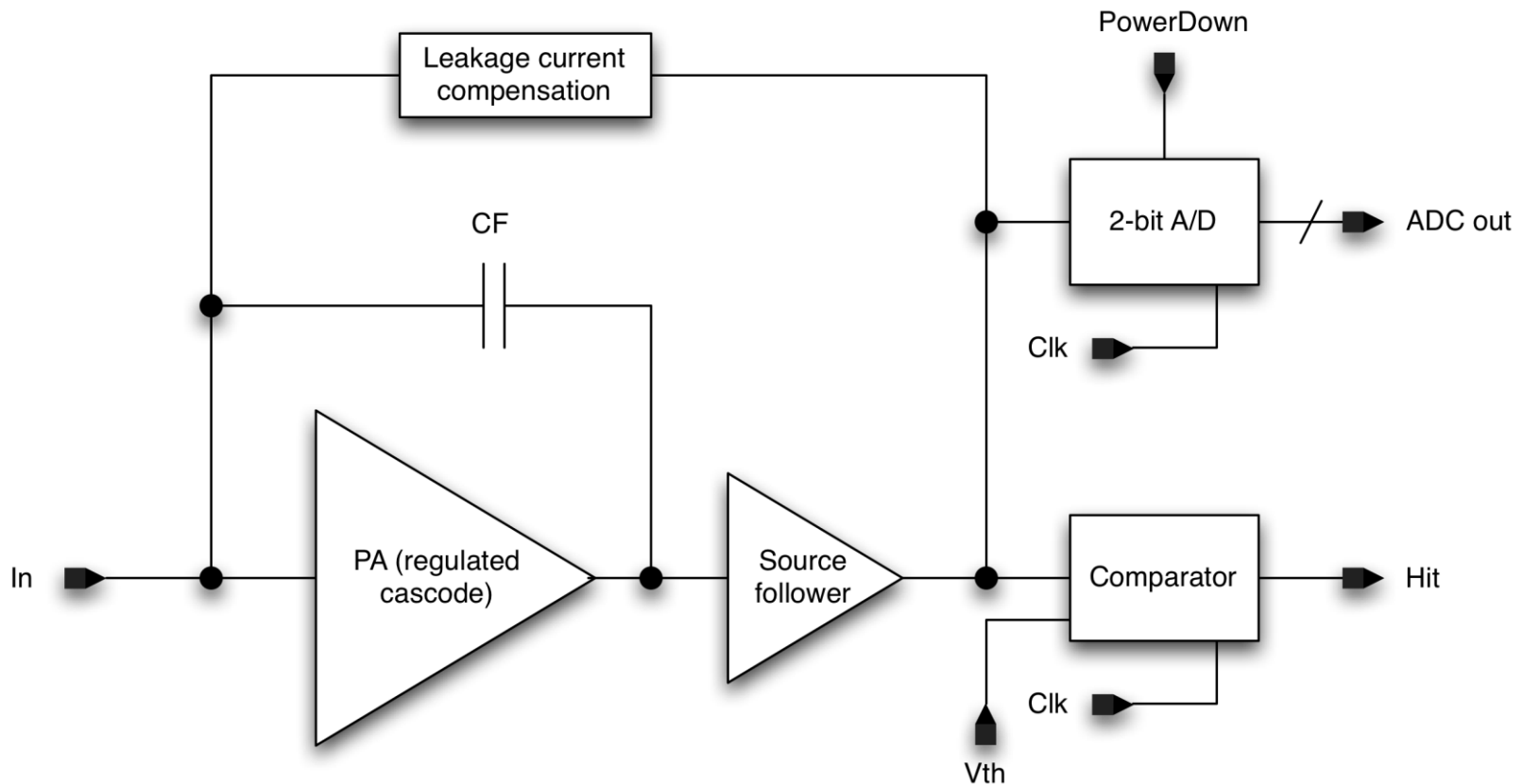
INFN - Fermi CMS Pixels (IFCP65)

Translation of FCP130 to 65nm by U. Bergamo (INFN)

Adaptation of FCP130nm concept to 65nm: IFCP65 (collaboration with INFN (U.Bergamo))

- ✓ **Accurate time allocation** of hits requires the discriminator to detect the smallest signal within the BXClk period
 - ✓ This may be difficult to achieve in a system with continuous time shaping → hits just above threshold can improperly be assigned to the **subsequent BXClk period**
 - ✓ **ToT systems** may requires several BXClk periods in order to perform full A-to-D conversion
 - ✓ Continuous time processing has to face **baseline drifts** due to charge pile-up or DC coupling of consecutive stages
- This AFE exploits the **synchronous environment** of the LHC to detect and determine incoming particle energy **within one BXClk period**

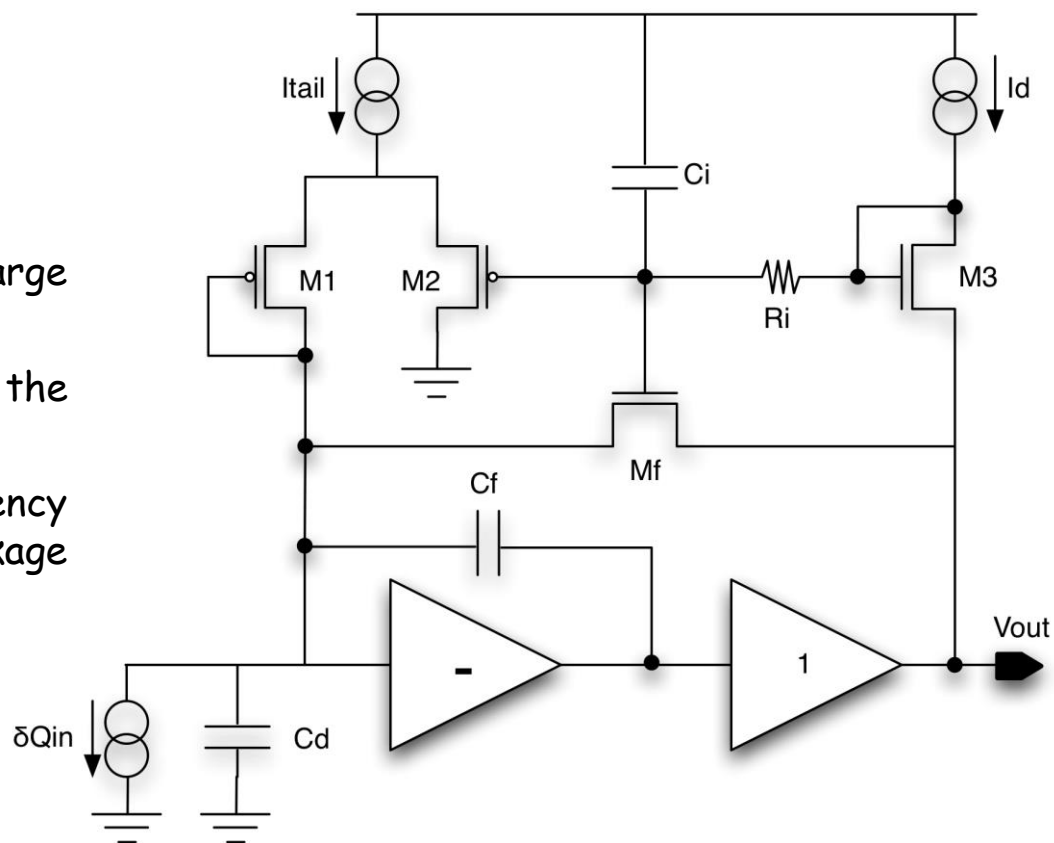
Pixel analog front-end



- ✓ **Synchronous** front-end with **zero dead time**
- ✓ Preamplifier (Regulated cascode) featuring a leakage current compensation circuit
- ✓ **Digital conversion** immediately after the preamplifier
- ✓ No in-pixel **charge injection** circuit. 15fF injection capacitance connected to the PA input

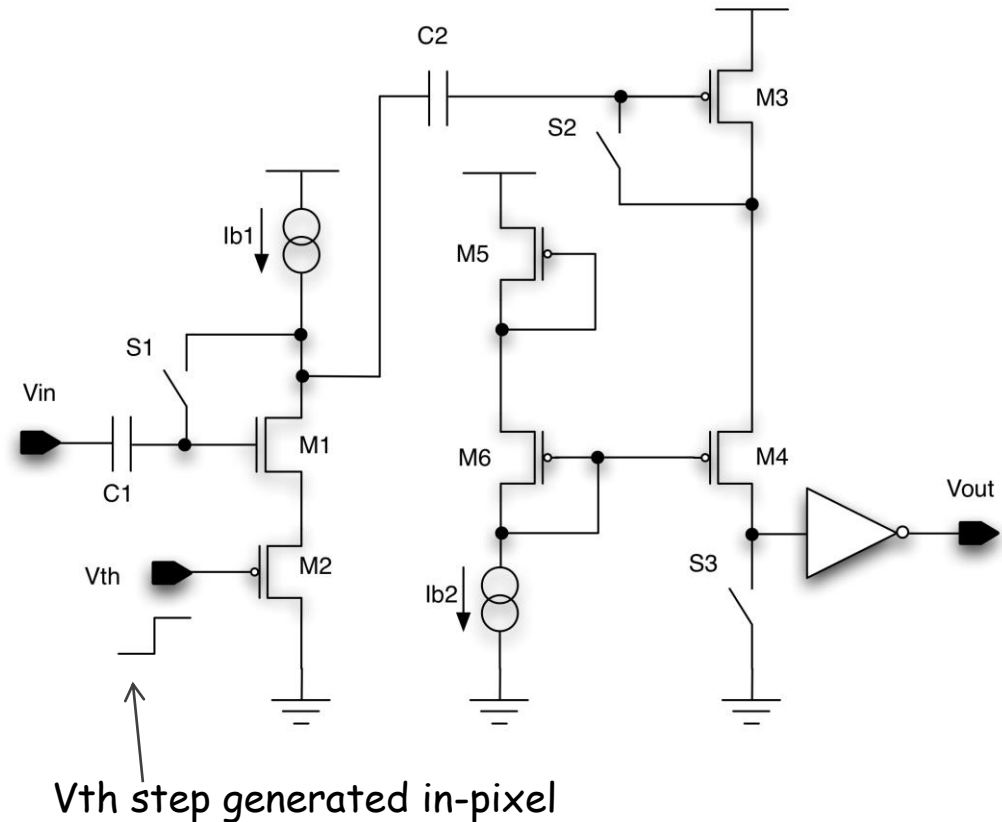
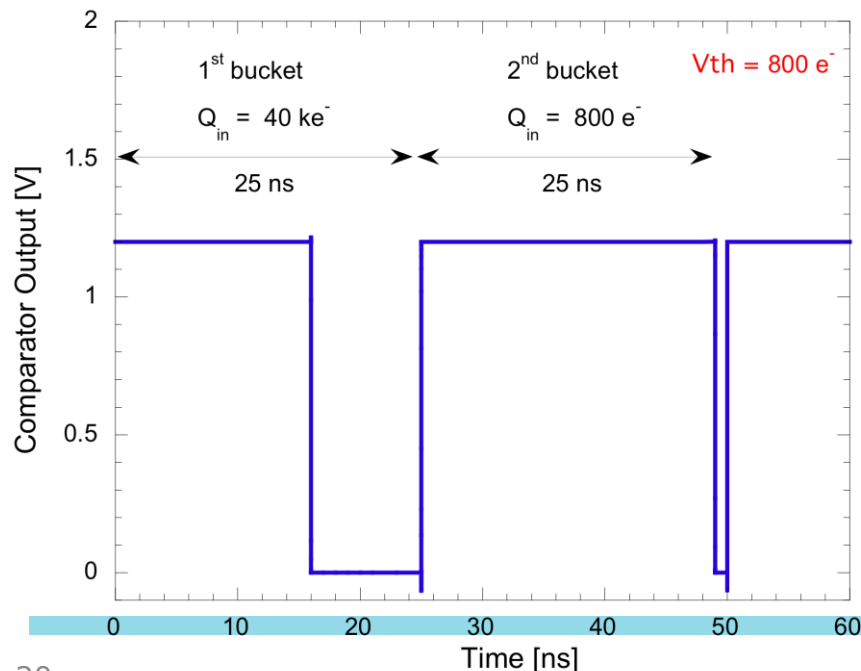
Charge sensitive amplifier

- ✓ **Regulated cascode** design
- ✓ Active feedback transistor M_f :
 - ✓ **$1/g_m$ resistor** for small signals
 - ✓ **Constant current source** for large signal.
 - ✓ M_1 provides a DC path for the **detector leakage current**
 - ✓ $R_i + C_i$ ensures low frequency operation of the leakage compensation circuit
- ✓ **Current consumption** $\sim 4.0 \mu A$



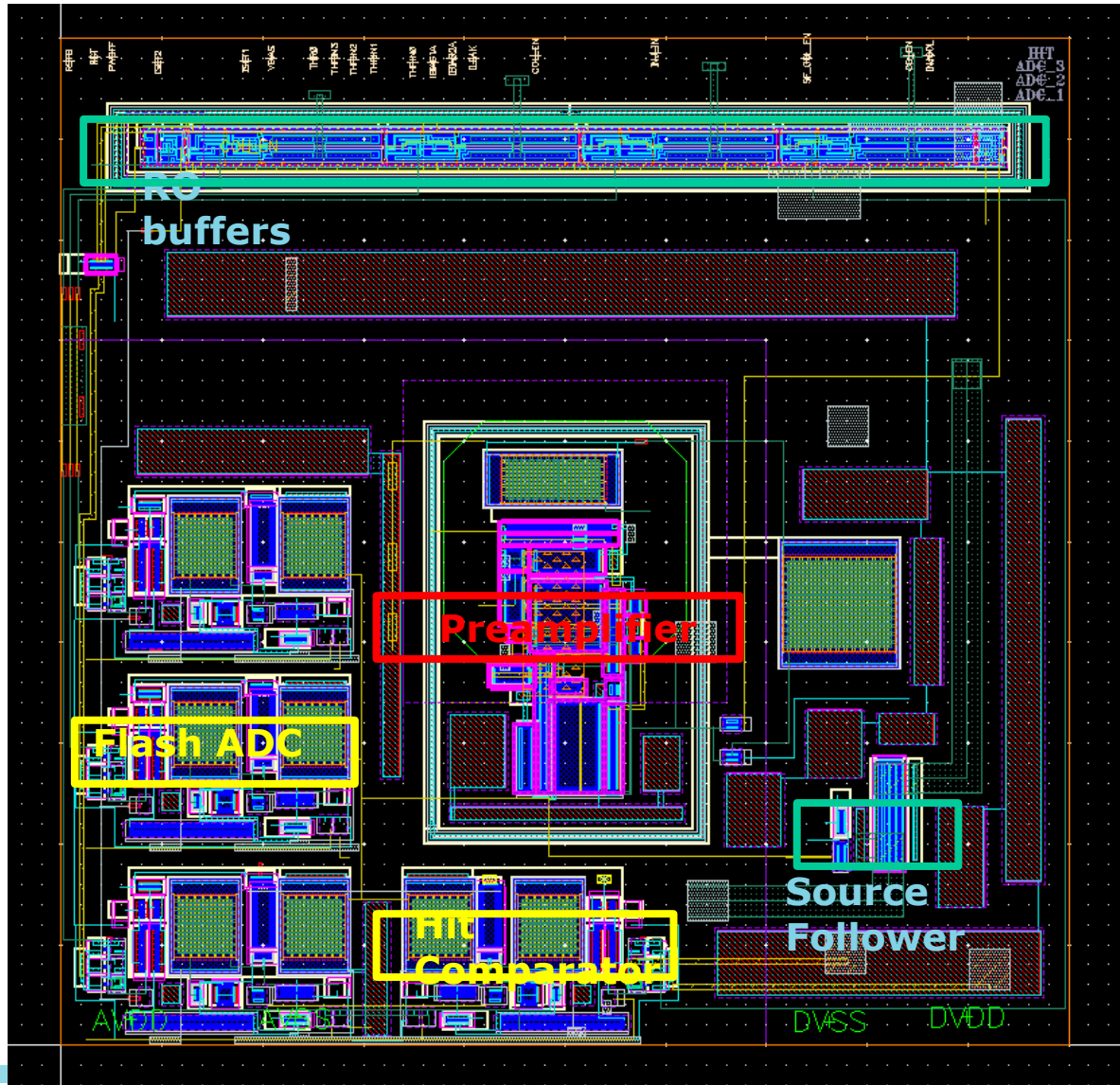
Comparator

- ✓ Compact, single-ended architecture
- ✓ **AC coupled** to the preamplifier
- ✓ **Correlated double sampling:**
 - ✓ Auto-zeroed
 - ✓ Increased pileup immunity
 - ✓ No need for trimming DAC



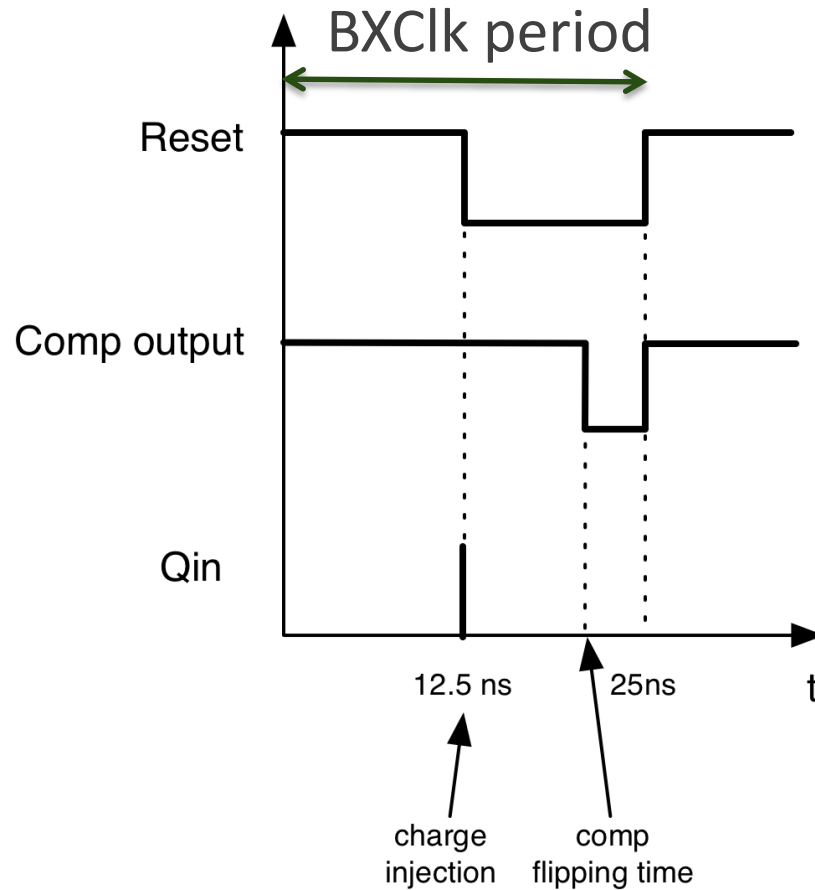
- ✓ 12.5ns reset phase; 12.5ns active comparison
- ✓ $\sim 1 \mu A$ current consumption

Layout



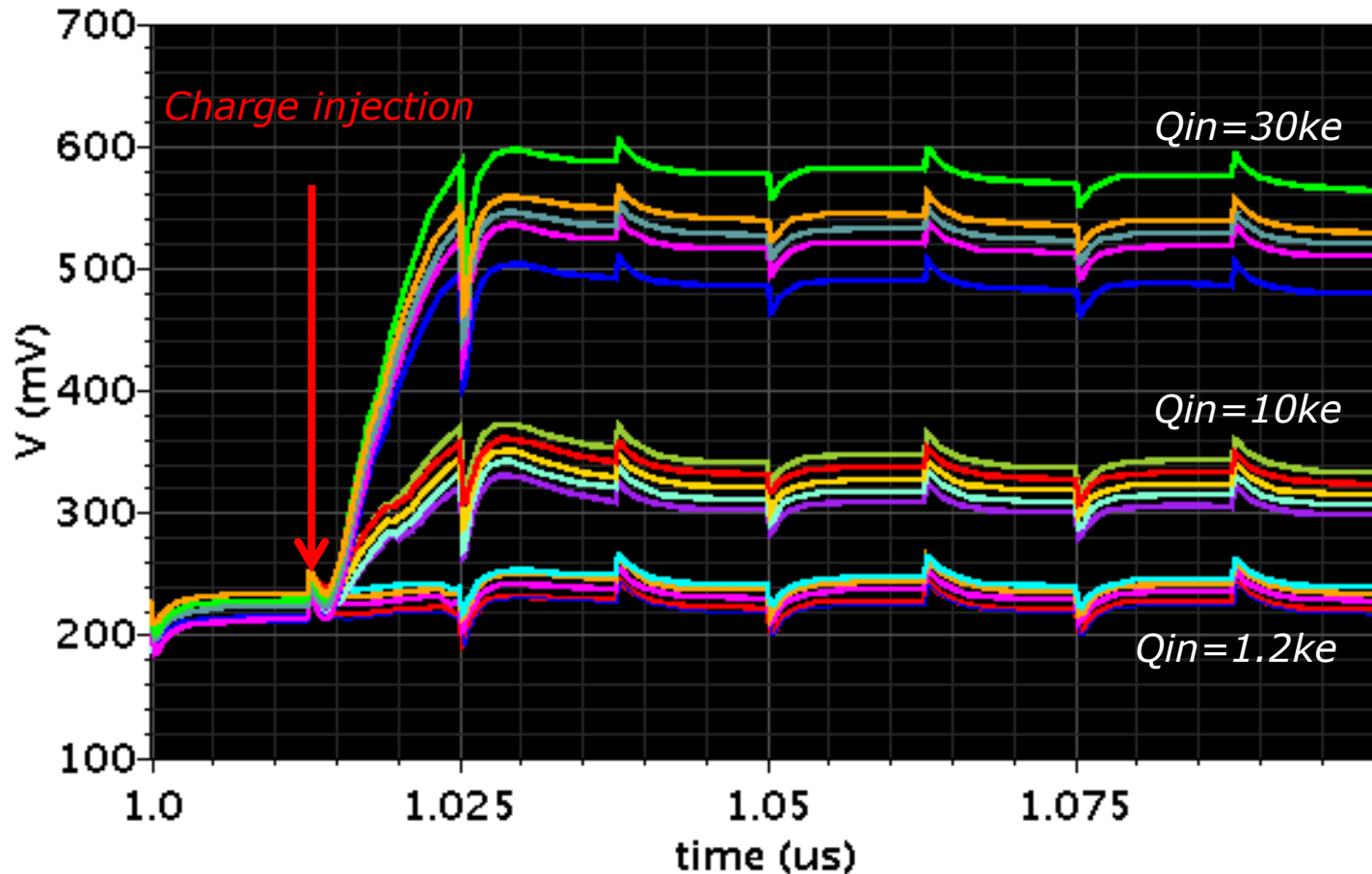
- ✓ RO buffers and Source follower included in the miniasic version of the AFE
- ✓ All the devices in the global P-substrate
- ✓ MIM feedback cap
- ✓ Nwell guard ring surrounding the preamplifier

Timing Diagram



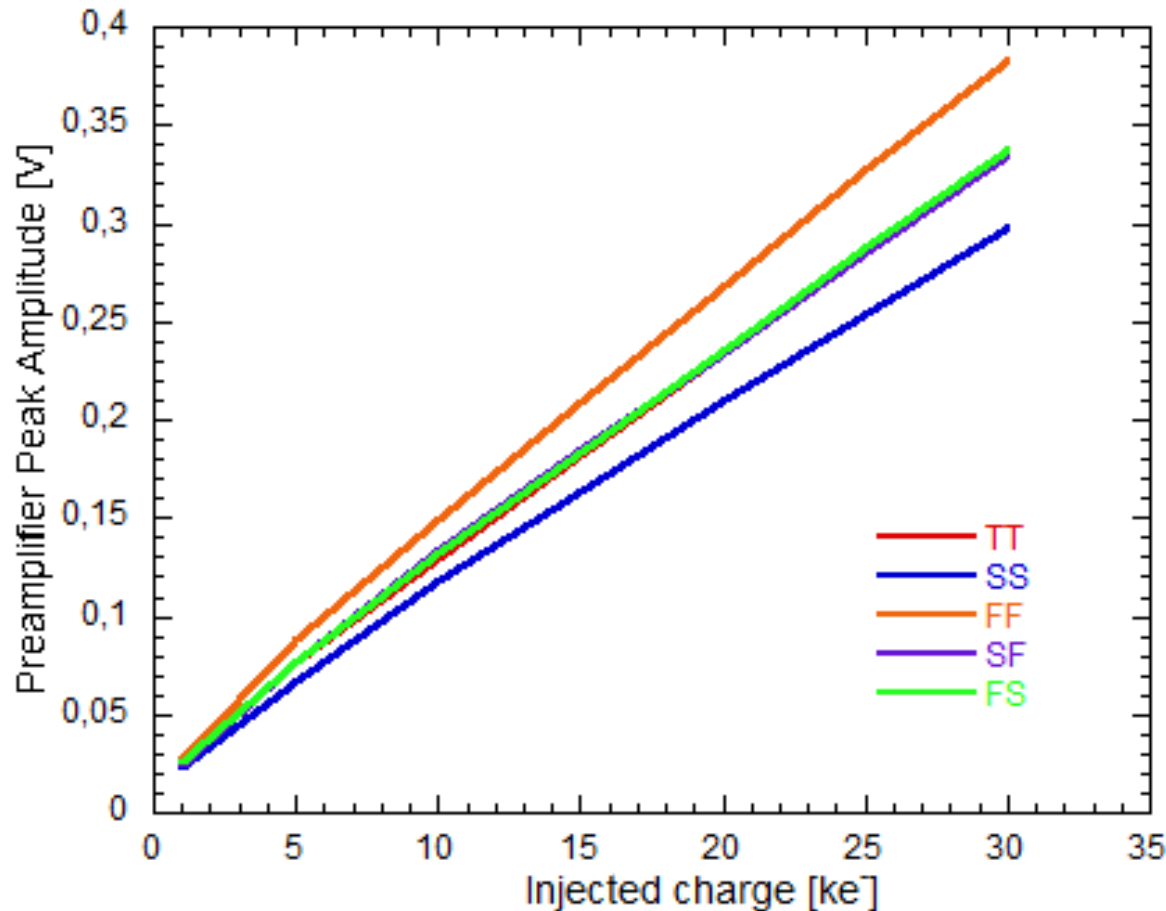
- **Charge injection** takes place as soon as the reset is released
- **40 MHz** reset signal

Preamplifier output - 4C simulations



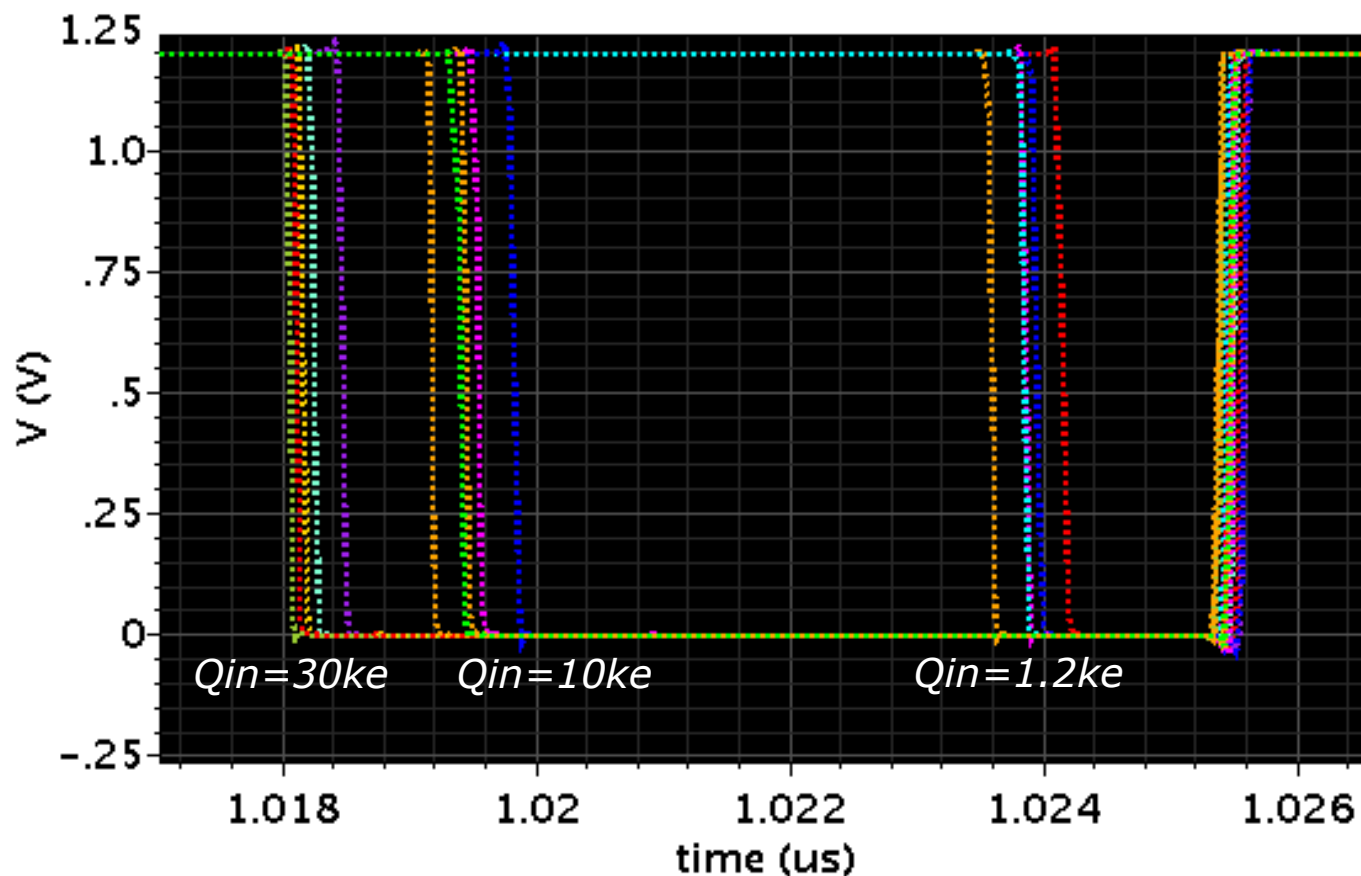
- **PA output** for $Q_{in}=1.2ke$ -, $10ke$ -, $30ke$. $CD=50fF$, $Q_{th}=600e^-$
- $\pm 14\%$ variation (wrt TT) in the **PA peak amplitude** (mainly due to the MIM feedback cap)

Preamplifier peak amplitude - 4C simulations



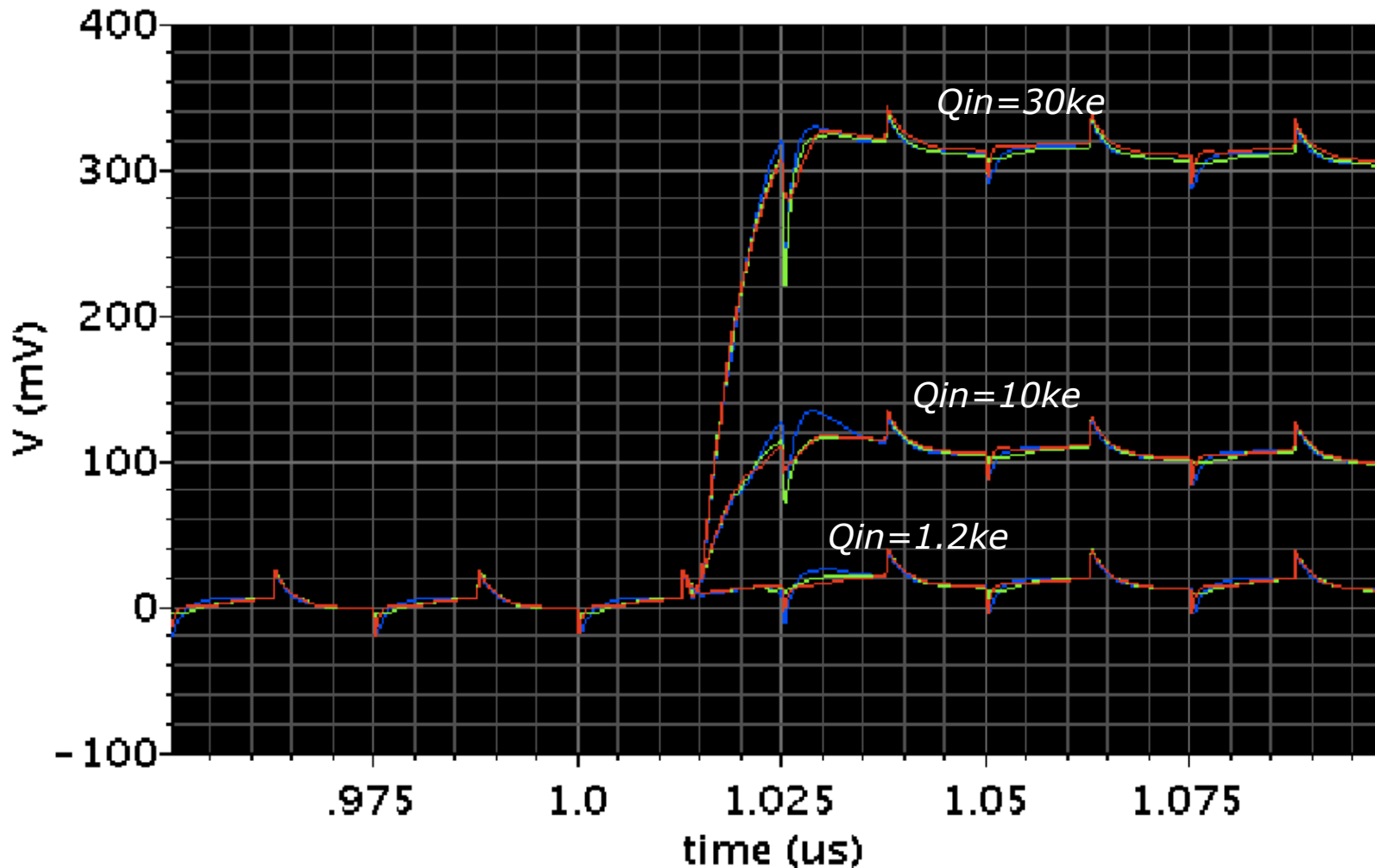
- **PA peak amplitude** as a function of the injected charge
- **Good linearity** in all the corners
- Non-negligible changes in **charge sensitivity** due to the MIM feedback cap

Comparator output - 4C simulations



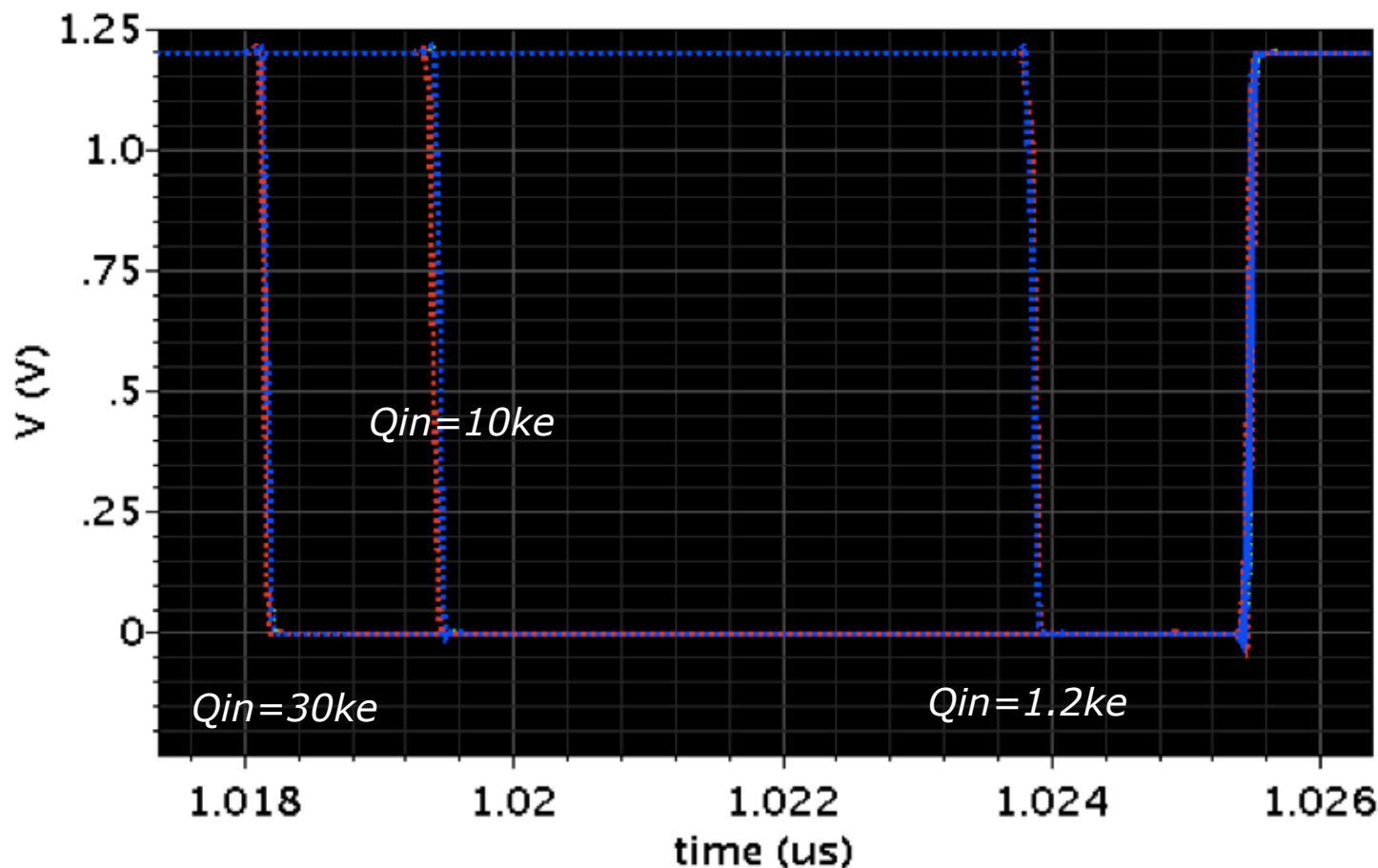
- **Comparator output** for $Q_{in}=1.2ke$ -, $10ke$ -, $30ke$. $CD=50fF$, $Q_{th}=600e$ -
- $< \pm 400ps$ changes (wrt to TT) in comparator flipping time

Preamplifier output - Radiation corners



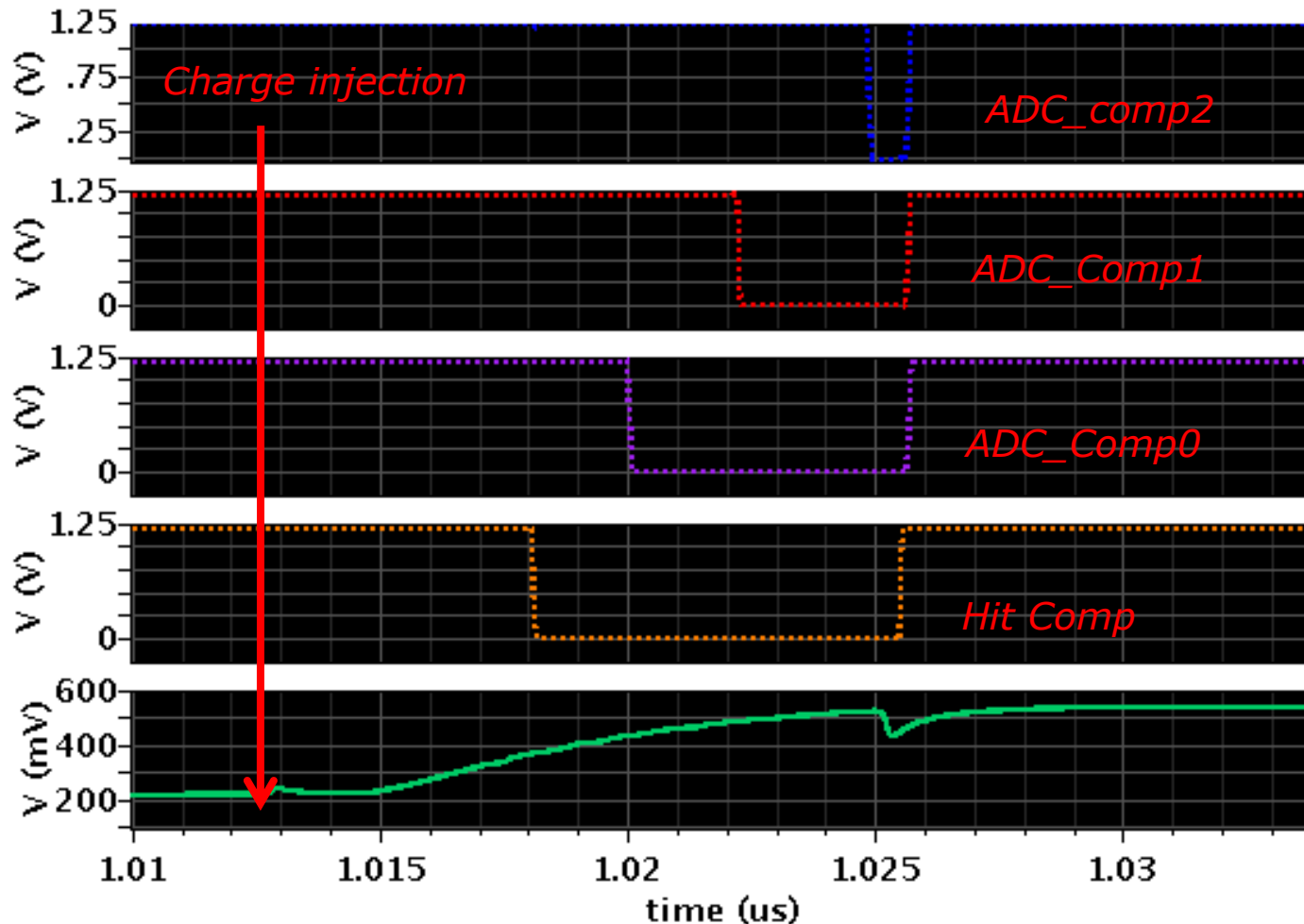
- PA output for $Q_{in}=1.2ke^-$, $10ke^-$, $30ke^-$. TT+200Mrad+500Mrad corners. CD=50fF
- Negligible changes in PA output response in the different corners

Comparator output - 500 Mrad corner



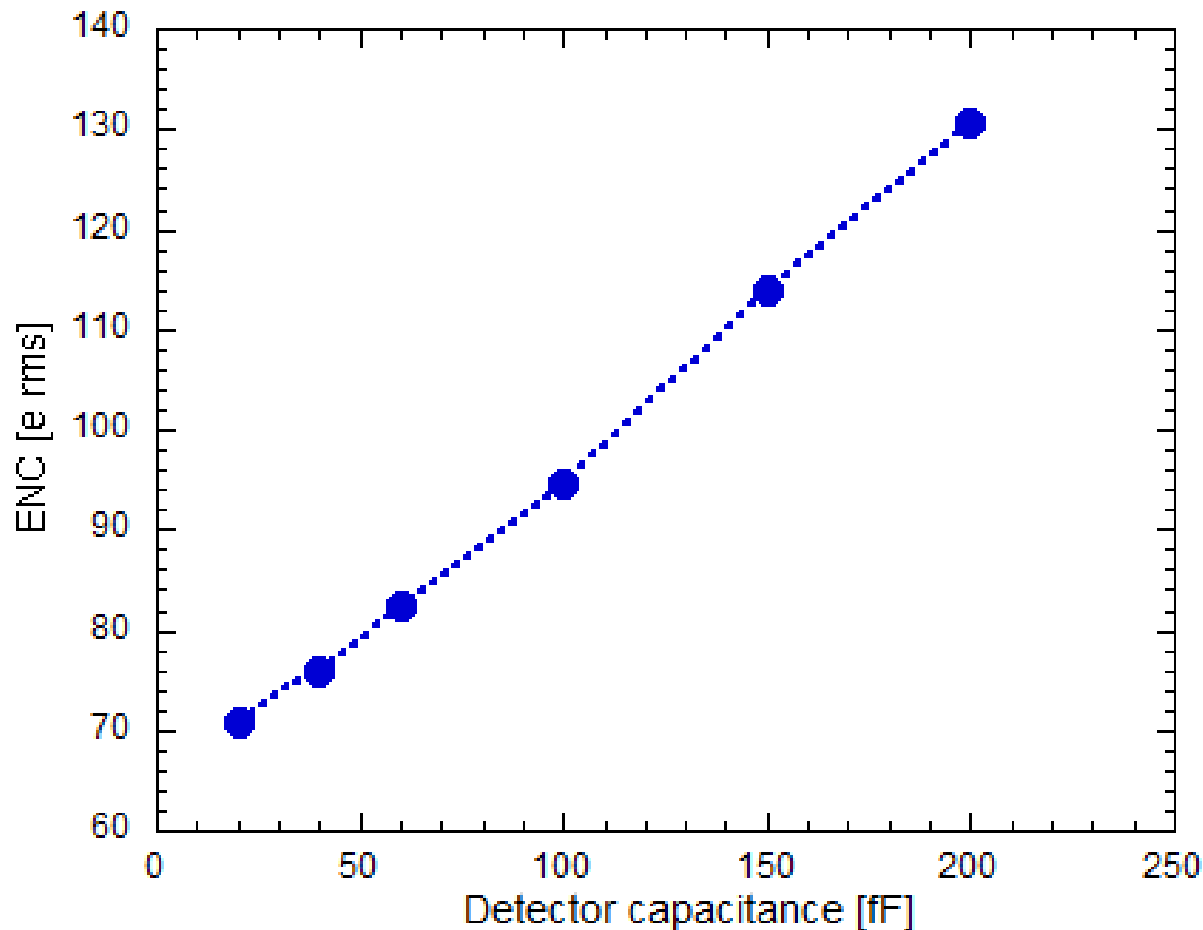
- **Comparator output** for $Q_{in}=1.2ke^-$, $10ke^-$, $30ke^-$. TT + 500Mrad corners. $CD=50fF$, $Q_{th}=600e^-$
- Negligible changes in **comparator flipping time**

Hit Comparator and ADC comparator outputs



- **Hit Comparator** and **ADC comparators** outputs for $Q_{in}=30\text{ke-}$
- Threshold for the different comparators can be **set up independently** by means of bias lines distributed through the matrix columns

Equivalent Noise Charge



- ENC as a function of CD @ $T=+27^\circ$. Evaluated at PA output (CDS effects not simulated here)
- $ENC \approx 80e$ @ $CD=50fF$.
- ENC obtained with a proportional calibration constant for small input charges (0 to 2ke)

Recap Table #1

	TT	TT 500 Mrad	SS	FF	FS	SF	spec
Charge sensitivity [mV/ke]	10.3	10.2	9.1	11.7	9.9	10.4	-
ENC rms [e]	79	79	82	76	83	77	$\ll 126$
Threshold dispersion $\sigma(\text{Qth})$ rms [e]	35						$\ll 126$
$\sqrt{\text{ENC}^2 + \sigma(\text{Qth})^2}$ [e]	86						≤ 126
In-time overdrive [e-]	Not applicable						≤ 600
Current consumption [$\mu\text{A}/\text{pixel}$]	7.4*	7.2					≤ 4
Delay time [ns]	10.8	12.1	11.0	10.5	10.8	10.9	-
ADC Conversion time [ns]	12.5	12.5	12.5	12.5	12.5	12.5	-

- Post-layout simulations, default configuration
- Detector capacitance $C_D=50$ fF, $T=27^\circ \text{C}$
- In-time overdrive \rightarrow "0" in this AFE
- Delay time (comp flipping time - charge inj time) $\rightarrow 600$ e-, $Q_{in}=1200$ e-

* ~ 5 $\mu\text{A}/\text{pixel}$ when in binary mode. Comparator dynamic current not included

Recap Table #2

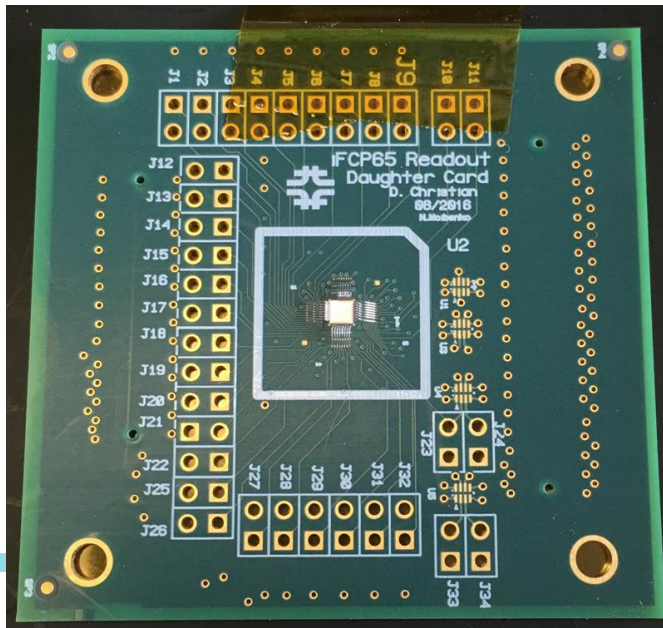
	27° C	- 20° C	spec
Charge sensitivity [mV/ke]	10.3	9.0	-
ENC rms [e]	79	82	$\ll 126$
In-time overdrive [e-]	Not applicable		≤ 600
Current consumption [μ A/pixel]	7.4*	7.2	≤ 4
Delay time [ns]	10.8	9.9	-
ADC conversion time [ns]	12.5	12.5	-

- Post-layout simulations, default configuration
- Detector capacitance $C_D=50$ fF, $T=27^\circ$ C
- In-time overdrive \rightarrow "0" in this AFE
- Delay time (comp flipping time - charge inj time) $\rightarrow 600$ e-, $Q_{in}=1200$ e-
- * ~ 5 μ A/pixel when in binary mode

32



- ✓ 16x16 matrix
- ✓ Charge injection and readout controlled via three independent SIPO shift registers
- ✓ 16 independent outputs (one for each row) to read out the pixel preamplifier output

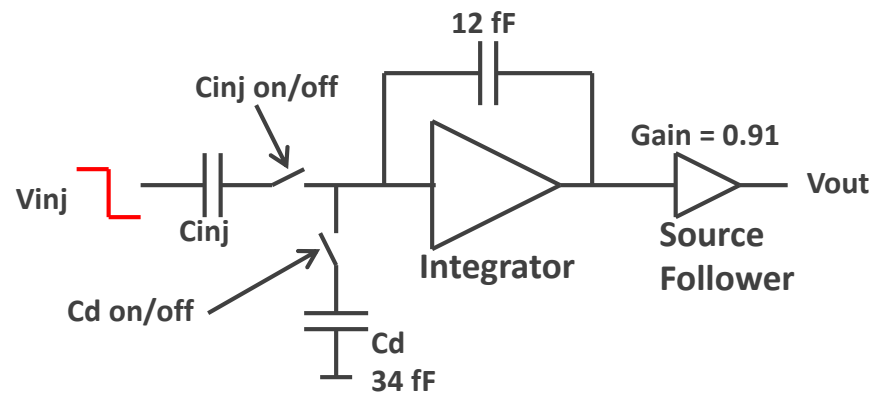


- ✓ Test boards fabricated and populated
- ✓ ASIC's wire bonded
- ✓ Tests started last week

Integrator Gain

Assumptions:

$C_{fb} = 12 \text{ fF}$, Source Follower gain = 0.91



“Measure” C_{inj} :

Apply a step input and measure V_{out} :

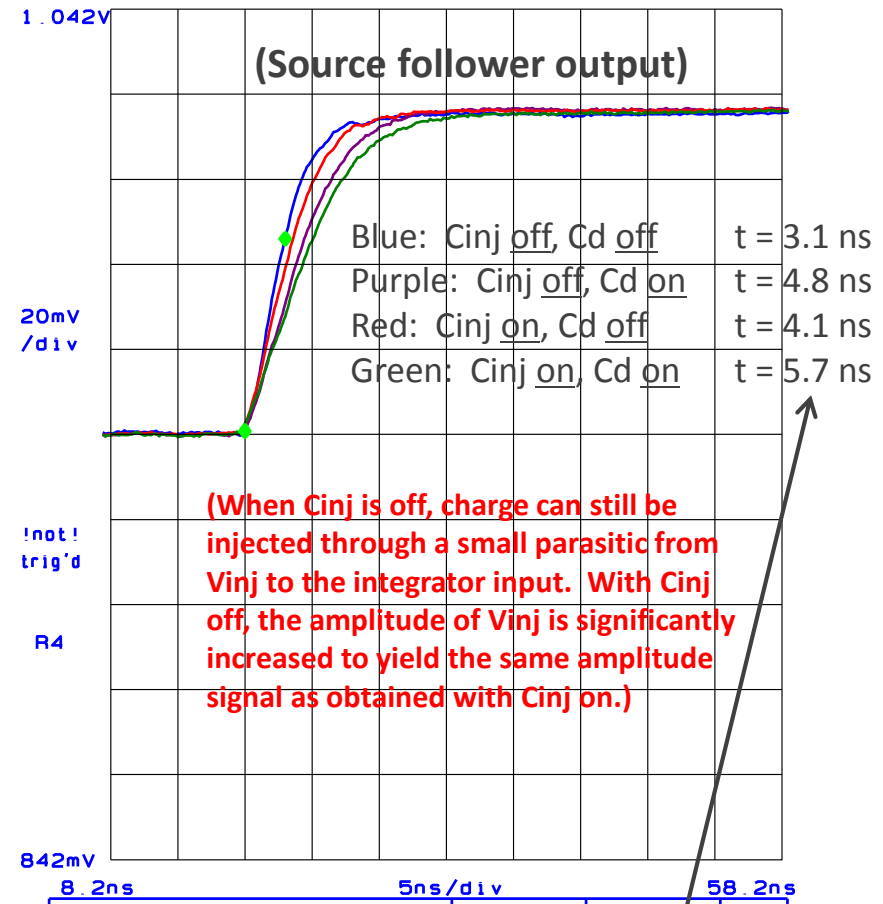
If $V_{inj} = -146 \text{ mV}$, then $V_{out} = 122.4 \text{ mV}$

Therefore: $C_{inj} = 11.1 \text{ fF}$.

Pixel-to-pixel gain variation across the array is less than 2% -- good.

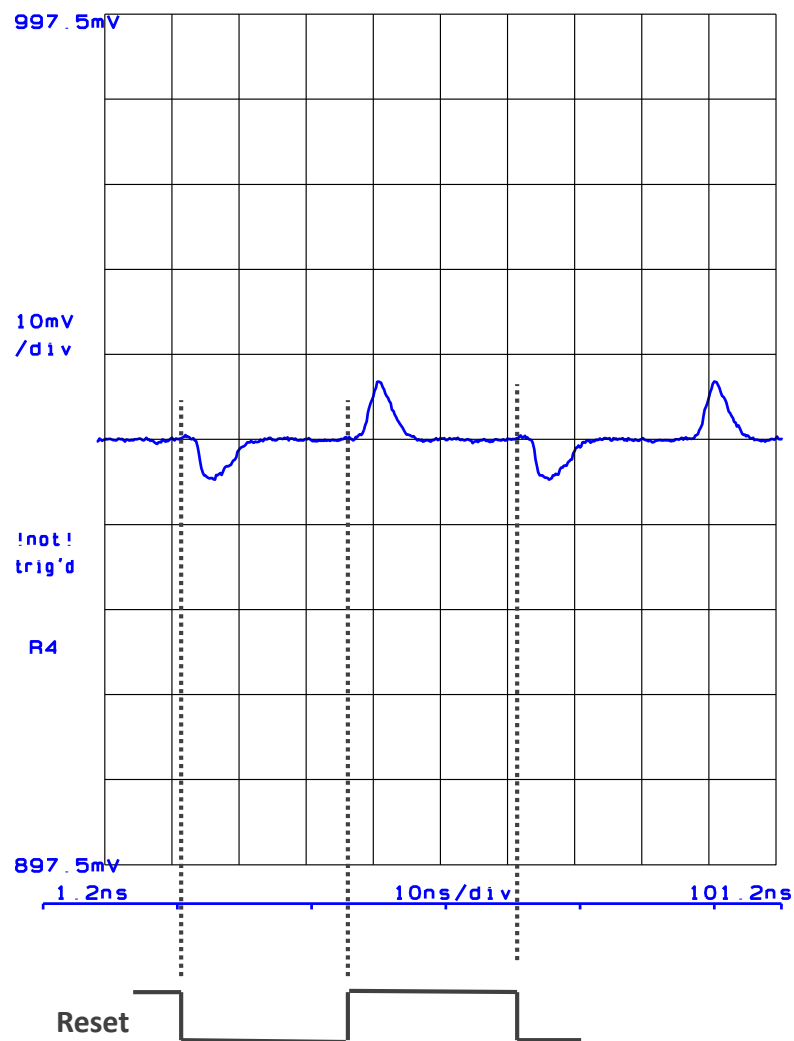
Integrator Time Response

($V_{inj} = 90 \text{ mV}$ with C_{inj} on)



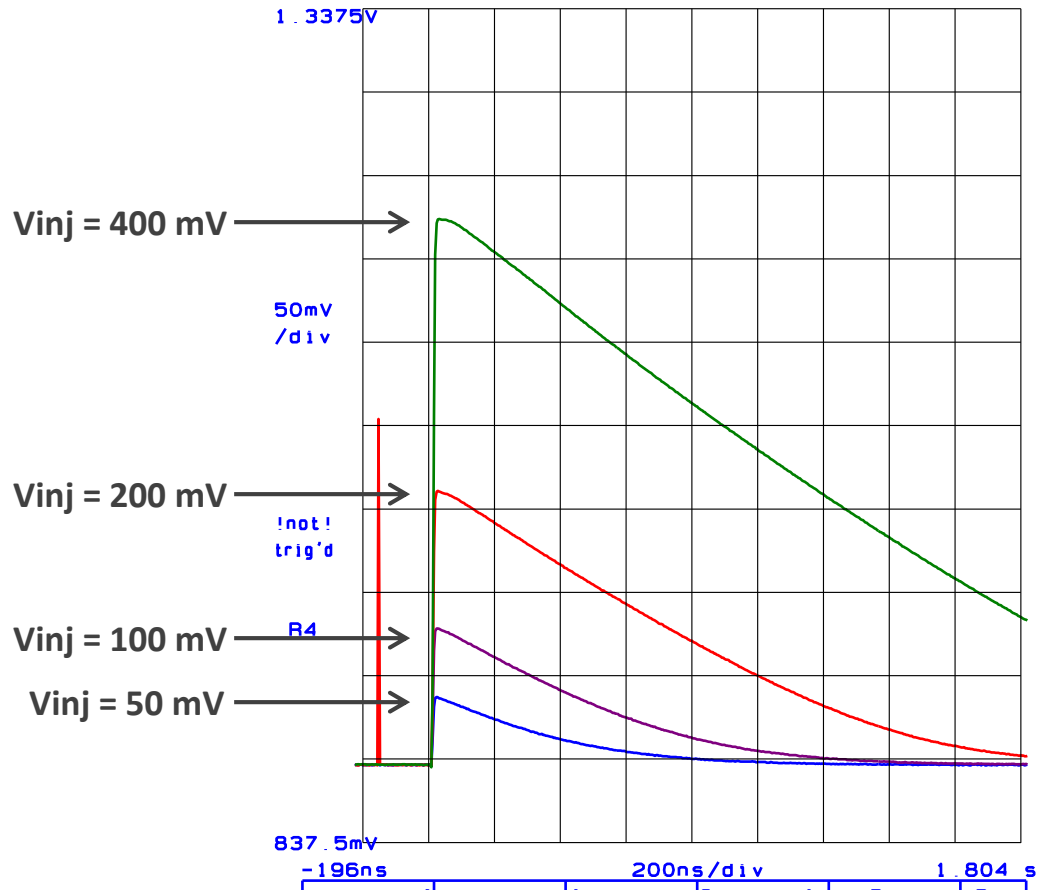
Time constant ($\sim 1 - 63\%$)

Integrator output while operating Reset (no signal)



Integrator return to baseline

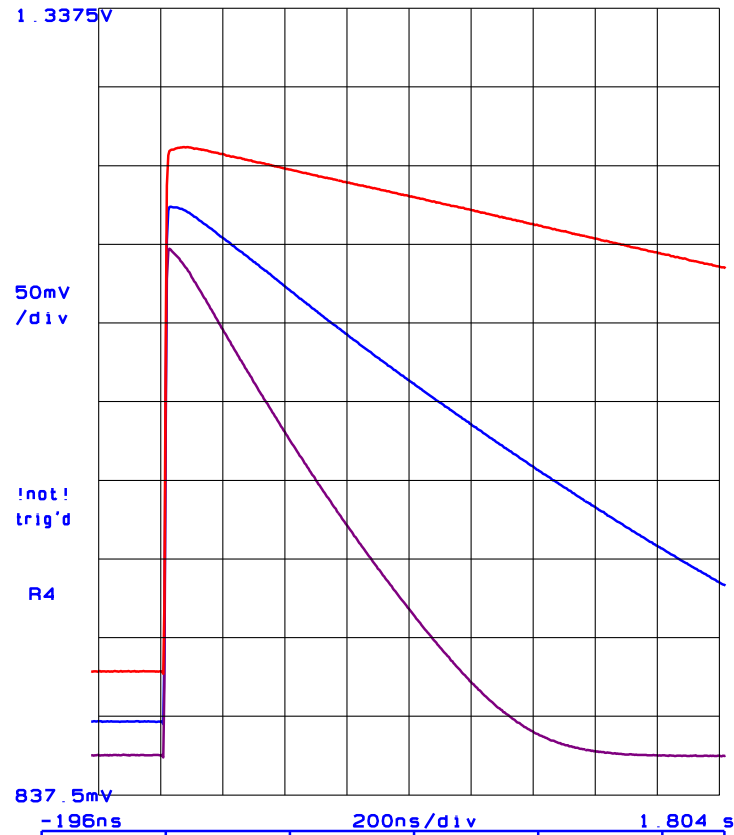
(Ileak at nominal setting)



Looks good

Vary I_{leak}

(V_{inj} = 400 mV)



Looks good



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RD53A:

Following slides from RD53A design review

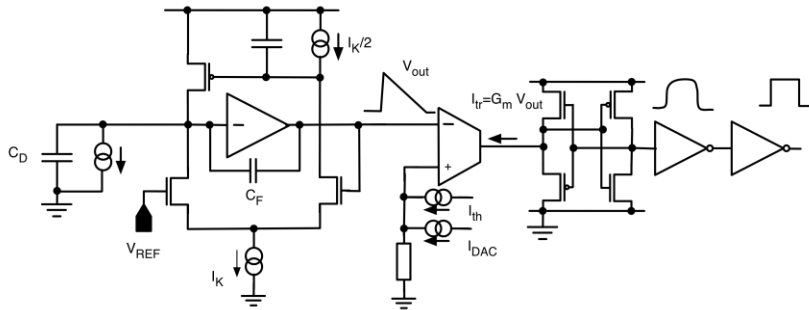
RD53A MUST demonstrate

- Small pixels: $50 \times 50 \mu\text{m}^2$
- Low in-time effective threshold: 1200e-
 - Very good digital/analog isolation
- ~4bit charge at high rate
- High hit rate: $3\text{GHz}/\text{cm}^2$
 - Dead time loss $< 1\%$
- Time walk: $< 25\text{ns}$
- Digital buffering/processing: $12.5\mu\text{s}$
- Trigger rate: 1MHz
- Acceptable power consumption: $< 3\text{W} + 1\text{W SLDO}$ ($< 1\text{W}/\text{cm}^2$)
- Serial powering
- High radiation tolerance: 500Mrad
- Working with bump-bonded sensors in test beams

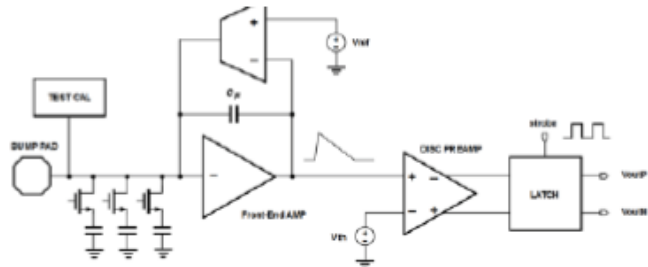
Defined in: <https://cds.cern.ch/record/2113263>

RD53A: Analog front-ends

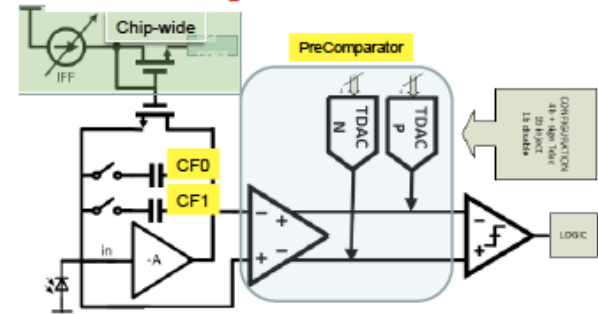
INFN Pavia/Bergamo design



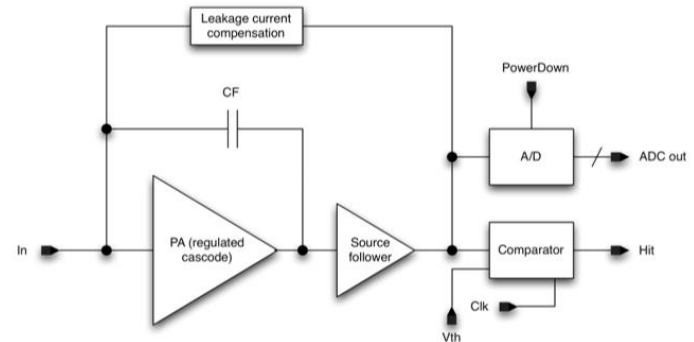
INFN Torino design



LBNL design in FE65-P2



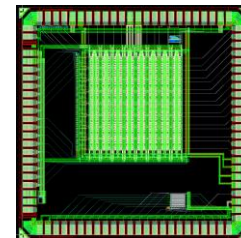
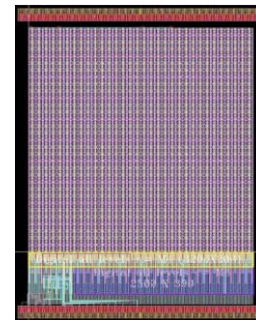
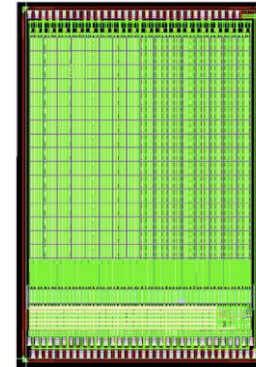
INFN-FNAL design

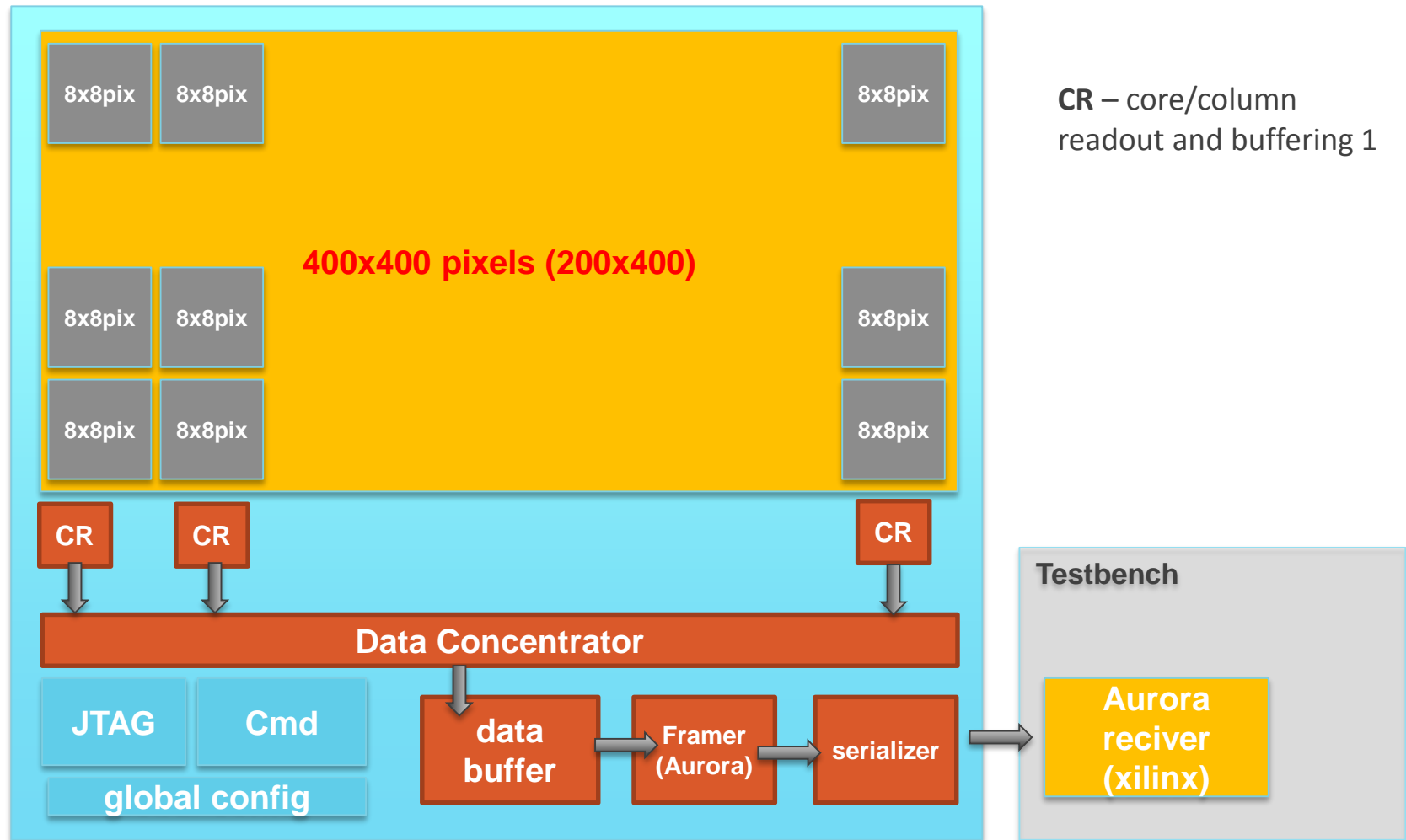


- **4 different AFEs.** Test results on available prototypes look good (also after irradiation) - (INFN-FNAL design not yet tested)
- **FE65-P2** and the **CHPIX65** demonstrators are going to provide essential information and experience in view of the integration of the analog FE in the RD53A chip. Test results on the FE65-P2 very encouraging
- The RD53A demonstrator will include several versions of the analog FE. They should be **fully tested** (also after irradiation) in their (almost) final version (schematic and layout) so that they qualify to be safely included in RD53A

65 nm CMOS analog front-end prototypes

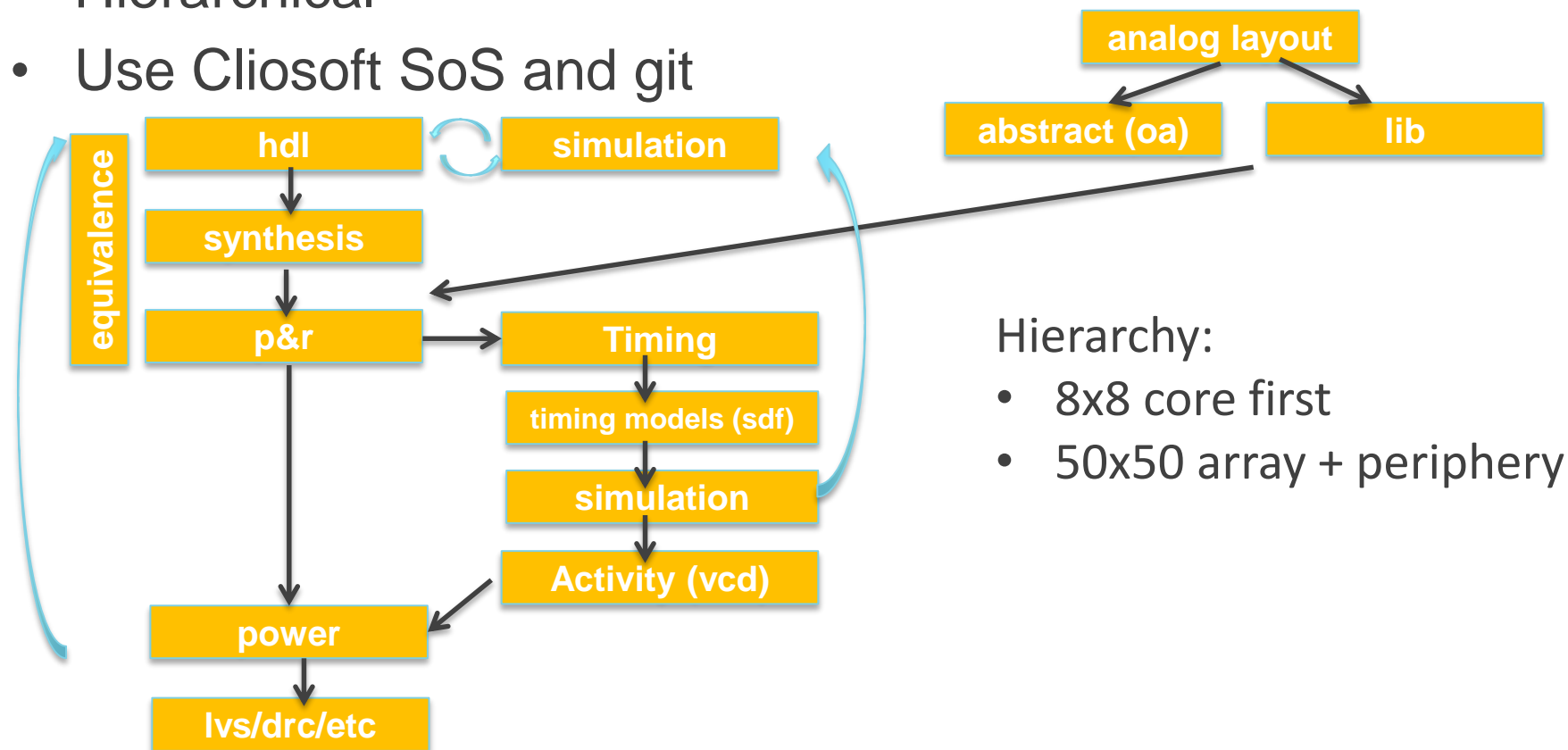
- **INFN** (Pavia, Torino) submitted (May 2015) small prototypes with two different versions (asynchronous, synchronous) of the analog front-end. Encouraging results from test
- These two different analog front-end will be included in the **CHIPIX65** demonstrator (end of June)
- Another design for the analog front-end (asynchronous) is included in the **FE65-P2** that is currently being tested, with promising results
- **Fermilab/INFN** recently submitted (May 2016) an analog front-end with zero dead time and Flash ADC; characterization has just started





Custom Design Methodology Flow

- OpenAccess mixed signal (modified flow CERN)
- Industry standard tools (complex and expensive)
- Hierarchical
- Use ClioSoft SoS and git



Pixel sensor and bump-bonding

- Signal, charge, pixel size, etc.
- Bump pad layout
- -----

RD53A chip: Jorgen, Maurice

- Specifications
- Documentation
- General organization

Test system: TBD (Bonn, CERN, Pisa, ?)

- Requirements, specifications
- Hardware, Firmware, Software
- Chip test/characterization: wafer level, chip level, beam tests
- Radiation testing

RD53A chip integration/verification: Flavio, Deputy: Tomasz

Floorplan: Flavio, Dario

- Pixel array, Bump pad
- EOC
- Power distribution
- Bias distribution
- Analog/digital isolation
- Integration/verification

Analog FEs (3/4) with biasing: Luigi, Valerio, Ennio, Dario, IP designers

- Specification/performance
- Interface (common)
- Analog isolation
- Digital/timing model
- Abstract
- Verification of block: Function, radiation, matching, etc.
- Shared database
- Integration in design flow
- Distribution of global analog signals
- Verification of integration

Monitoring: Francesco, Mohsine, IP designers

- Specification/performance
- Interface
- Analog isolation
- Digital/ timing model
- Abstract
- Verification of block: Function, radiation, matching, etc.
- Shared database
- Integration in design flow
- Verification of integration

Digital: Tomasz

- **Simulation Framework: Elia, Sara,**
 - Framework
 - Hit generation/ import MC
 - Reference model / score board
 - Monitoring/verification tools
 - Generic behavioural pixel chip
 - SEU injection
- **Architecture: Elia, Sara, (Andrea, Luca)**
 - Evaluation – choice: Performance, Power, Area, ,
 - Simulation/Optimization
 - **Functional Verification**
 - SEU immunity
- **Pixel array/pixel regions: Sara, (Andrea)**
 - Latency buffer
 - Core/column bus
- **Readout/control interface: Roberto, Paris**
 - Data format/protocol
 - Rate estimation / Compression
 - Implementation
- **Configuration: Roberto, Mohsine, (Luca)**
 - External/internal interface
 - Implementation
- **Implementation: Dario, Sara, (Luca, Andrea),**
 - **Script based to “quickly” incorporate architecture/RTL changes**
 - RTL - Synthesis
 - Functional verification
 - SEU verification
 - P&R
 - FE/IP integration
 - Clock tree synthesis
 - Timing verification
 - Power verification
 - Physical verification
 - Final chip submission

Digital lib.: Dario, Sandeep, Mohsine

- Customized rad tol library
- Liberty files (function, timing, etc.) Characterized for radiation
- Custom cells (Memory, Latch, RICE)
- Integration with P&R
- Radiation tolerance
- Integration in design kit

Power: Michael, Sara, Stella, Flavio

- Shunt-LDO integration
- On-chip power distribution
- Optimization for serial powering
- System level power aspects
- Power Verification

IO PAD frame: Hans

- Wirebonding pads, ESD, SLVS, Serial readout, **Shunt-LDO**, analog test input/output

Testing/Yield optim.: Sandeep, Luca

- Testability
- Scan path
- BIST
- Redundancy
- Bump-bonding test/verification

Support and services:

- Tools, design kit: Wojciech, Sandeep
 - ClioSoft repository: **Elia, Dario, Sandeep, Wojciech**
 - Radiation effects and models: **Mohsine**
- 10/18/2016

Questions?
